

Change in the parameters of electron-irradiated 4H-SiC Schottky diodes as a function of the time during low-temperature isothermal annealing

Korolkov, Oleg; Kozlovski, Vitali V.; Lebedev, Alexander A.; **Toompuu, Jana**; **Sleptsuk, Natalja**; **Rang, Toomas** Silicon Carbide and Related Materials 2018 : 12th European Conference on Silicon Carbide and Related Materials (ECSCRM 2018) : Selected, peer reviewed papers from the European Conference on Silicon Carbide and Related Materials (ECSCRM 2018), September 2-6, 2018, Birmingham, UK 2019 / p. 734-737 <https://doi.org/10.4028/www.scientific.net/MSF.963.734> [Conference proceeding at Scopus](#) [Article at Scopus](#)

Comparative results of low temperature annealing of lightly doped n-layers of silicon carbide irradiated by protons and electrons

Kozlovski, Vitali V.; **Korolkov, Oleg**; Lebedev, Alexander A.; **Toompuu, Jana**; **Sleptsuk, Natalja** Silicon Carbide and Related Materials 2019 : 18th International Conference on Silicon Carbide and Related Materials 2019 (ICSCRM 2019), Kyoto, Japan, September 29 - October 4, 2019 2020 / p. 231-236 <https://doi.org/10.4028/www.scientific.net/MSF.1004.231> [Conference Proceedings at Scopus](#) [Article at Scopus](#)

Degradation of 600-V 4H-SiC Schottky diodes under irradiation with 0.9 MeV electrons

Lebedev, Alexander A.; Davidovskaja, Klavdia; Kozlovski, Vitali V.; **Korolkov, Oleg**; **Sleptsuk, Natalja**; **Toompuu, Jana** Silicon Carbide and Related Materials 2016 : selected, peer reviewed papers from the 11th European Conference on Silicon Carbide and Related Materials 2016 (ECSCRM 2016), September 25-29, 2016, Halkidiki, Greece 2017 / p. 447-450 : ill <https://doi.org/10.4028/www.scientific.net/MSF.897.447> [Conference proceedings at Scopus](#) [Article at Scopus](#)

Degradation of 600-V 4H-SiC Schottky diodes under irradiation with 0,9 MeV electrons

Lebedev, Alexander A.; Davydovskaja, K. S.; Kozlovski, Vitali V.; **Korolkov, Oleg**; **Sleptsuk, Natalja**; **Toompuu, Jana** 11th European Conference on Silicon Carbide and Related Materials : September 25-29, 2016, Porto Carras Grand Resort, Halkidiki, Greece : [poster session] 2016 / p. 49

Dependence of the carrier removal rate in 4H-SiC PN structures on irradiation temperature

Lebedev, Alexander A.; Davydovskaja, Klavdia S.; Kozlovski, Vitali V.; **Korolkov, Oleg**; **Sleptsuk, Natalja**; **Toompuu, Jana** Silicon Carbide and Related Materials 2018 : 12th European Conference on Silicon Carbide and Related Materials (ECSCRM 2018) : Selected, peer reviewed papers from the European Conference on Silicon Carbide and Related Materials (ECSCRM 2018), September 2-6, 2018, Birmingham, UK 2019 / p. 730-733 <https://doi.org/10.4028/www.scientific.net/MSF.963.730> [Conference proceeding at Scopus](#) [Article at Scopus](#)

Influence of the proton irradiation temperature on the characteristics of high-power high-voltage silicon carbide schottky diodes

Kozlovski, Vitali V.; **Korolkov, Oleg**; Davydovskaja, Klavdia S.; Lebedev, Alexander A.; Levinshtein, Michael E.; **Sleptsuk, Natalja**; Strel'Chuk, Anatolii M.; **Toompuu, Jana** Technical Physics Letter 2020 / p. 287 - 289 <https://doi.org/10.1134/S1063785020030244> [Journal metrics at Scopus](#) [Article at Scopus](#) [Journal metrics at WOS](#) [Article at WOS](#)

Low-temperature annealing of lightly doped n-4H-SiC layers after irradiation with fast electrons

Korolkov, Oleg; Kozlovski, Vitali V.; Lebedev, Alexander A.; **Sleptsuk, Natalja**; **Toompuu, Jana**; **Rang, Toomas** Semiconductors 2019 / p. 975-978 <https://doi.org/10.1134/S1063782619070133> [Journal metrics at Scopus](#) [Article at Scopus](#) [Journal metrics at WOS](#) [Article at WOS](#)

SiC schottky diode rectifier bridge represented as the diffusion-welded stack

Korolkov, Oleg; Kozlovski, Vitali V.; Lebedev, Alexander A.; **Land, Raul**; **Sleptsuk, Natalja**; **Toompuu, Jana**; **Rang, Toomas** Silicon Carbide and Related Materials 2016 : selected, peer reviewed papers from the 11th European Conference on Silicon Carbide and Related Materials 2016 (ECSCRM 2016), September 25-29, 2016, Halkidiki, Greece 2017 / p. 697-700 : ill <https://doi.org/10.4028/www.scientific.net/MSF.897.697> [Conference proceedings at Scopus](#) [Article at Scopus](#)